

isc Silicon PNP Transistor

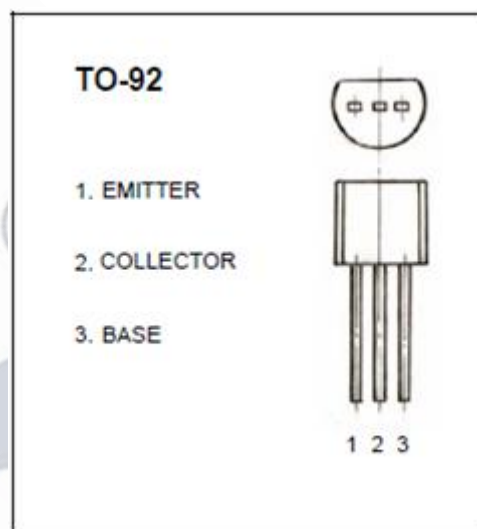
2SA1013

DESCRIPTION

- High Voltage and High Current
 $V_{ce0} = -160V(\text{Min.})$
- Excellent hFE Linearity
- Low Noise
- Complement to Type 2SC2383
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Audio frequency general purpose amplifier Applications
- Driver stage amplifier applications.


ABSOLUTE MAXIMUM RATINGS($T_a = 25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-160	V
V_{CEO}	Collector-Emitter Voltage	-160	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current	-1	A
I_B	Base Current	-500	mA
P_C	Collector Power Dissipation @ $T_c = 25^\circ\text{C}$	900	mW
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^\circ\text{C}$

isc Silicon PNP Transistor**2SA1015****ELECTRICAL CHARACTERISTICS** $T_c=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -500\text{mA}$; $I_B = -50\text{mA}$			-1.5	V
I_{CBO}	Emitter Cutoff Current	$V_{CB} = -150\text{V}$; $I_E = 0$			-1.0	μA
I_{EBO}	Collector Cutoff Current	$V_{EB} = -6\text{V}$; $I_C = 0$			-1.0	μA
h_{FE}	DC Current Gain	$I_C = -200\text{mA}$; $V_{CE} = -5\text{V}$	60		200	

◆ h_{FE} Classifications

R	O
60-120	100-200